L	Hits	Search Text	DB	Time stamp
Number				
-	227	438/658.ccls.	USPAT	2003/11/18
			1	10:36
-	137	438/658.ccls. and conductive	USPAT	2003/11/18
	406	420/650	**************************************	10:36
-	136	438/658.ccls. and conductive and layer	USPAT	2003/11/18
	60	420/CEO mala and manduative and lawar	USPAT	10:37 2003/11/18
-	68	438/658.ccls. and conductive and layer and via	USPAI	10:37
_	31	438/658.ccls. and conductive and layer	USPAT	2003/11/18
	J.	and via and electromigration	00	10:37
_	5	438/658.ccls. and conductive and layer	USPAT	2003/11/18
	-	and via and electromigration and dopant		10:37
_	1	438/658.ccls. and conductive and layer	USPAT	2003/11/18
		and via and electromigration and dopant		10:38
		and aluminum and concentrat\$4 and atomic		
-	2	438/658.ccls. and conductive and layer	USPAT	2003/11/18
		and via and electromigration and dopant		12:27
	_	and aluminum and concentrat\$4	TICDAM.	2003/11/24
_	5	438/658.ccls. and conductive and layer and via and electromigration and dopant	USPAT	11:49
		and via and electromigration and dopant and aluminum		11.49
_	51	438/658.ccls. and "conductive layer"	USPAT	2003/11/21
-	]	4307030.CCIS. and Conductive Tayor	002112	14:11
_	50	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate		14:11
_	21	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate and "dielectric layer"		14:11
-	15	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate and "dielectric layer" and		14:11
		"barrier layer"	110000	2002/11/21
_	12	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21 14:12
		substrate and "dielectric layer" and "barrier layer" and via		14.12
	0	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
-		substrate and "dielectric layer" and	002112	14:12
		"barrier layer" and via and dopant		
_	6		USPAT	2003/11/21
		substrate and "dielectric layer" and		14:14
		"barrier layer" and via and dop\$4		
-	6	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate and "dielectric layer" and		14:15
		"barrier layer" and via and dop\$4 and		
	2	electromigration 438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
-	-	substrate and "dielectric layer" and	OSTAL	15:19
		"barrier layer" and via and dop\$4 and		
		electromigration and atomic		
_	0	438/658.ccls. and "conductive layer" and	USPAT	2003/11/21
		substrate and "dielectric layer" and		15:19
		"barrier layer" and via and dop\$4 and		
		electromigration and atomic and implant		2002/33/04
-	2		USPAT	2003/11/24
		and via and electromigration and dopant		11:49
	_	and aluminum and ion	USPAT	2003/11/24
-	2	438/658.ccls. and conductive and layer and via and electromigration and dopant	OSEMI	11:50
		and aluminum and ion and gas		
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